

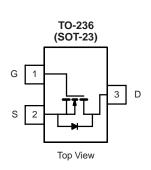
WST4040-VB Datasheet N-Channel 40 V (D-S) MOSFET

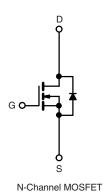
PRODUCT SUMMARY				
V _{DS} (V)	40			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.035			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.040			
I _D (A)	4.8			
Configuration	Single			

FEATURES

- Trench Power MOSFET
- 100 % R_g and UIS Tested







ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)						
PARAMETER		SYMBOL	LIMIT	UNIT		
Drain-Source Voltage		V_{DS}	40	.,,		
Gate-Source Voltage		V _{GS}	± 20	V		
Continuous Drain Current	T _C = 25 °C	1	4.8			
	T _C = 125 °C	l _D	3.6			
Continuous Source Current (Diode Conduct	Is	3.8	Α			
Pulsed Drain Current ^a	I _{DM}	20				
Single Pulse Avalanche Current	L = 0.1 mH	l _{AS}	13			
Single Pulse Avalanche Energy	L = U.1 Min	E _{AS}	8	mJ		
Maximum Power Dissipation ^a	T _C = 25 °C	D	3	W		
	T _C = 125 °C	- P _D	1	VV		
Operating Junction and Storage Temperatu	T _J , T _{stg}	-55 to +175	°C			

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount ^b	R_{thJA}	166	°C/W	
Junction-to-Foot (Drain)	<u>.</u>		50	C/VV	

Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. When mounted on 1" square PCB (FR-4 material).

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static	•							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		40	-	-	.,	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_D = 250 \mu A$		2.0	2.5	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA	
		V _{GS} = 0 V	V _{DS} = 40 V	=.	-	1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 40 V, T _J = 125 °C	=.	-	50	μA	
		$V_{GS} = 0 V$	V _{DS} = 40 V, T _J = 175 °C	-	-	150		
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	10	-		Α	
		V _{GS} = 10 V	I _D = 3.9 A	-	0.035	-	Ω	
Drain Cauras On State Besistance	В	V _{GS} = 10 V	I _D = 3.9 A, T _J = 125 °C	=.	0.045	-		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 3.9 A, T _J = 175 °C	-	0.065	-		
		V _{GS} = 4.5 V	I _D =3.3 A	-	0.040	-		
Forward Transconductanceb	9 _{fs}	V _{DS} = 15 V, I _D =3.9 A		-	30	-	S	
Dynamic ^b	<u> </u>							
Input Capacitance	C _{iss}			-	442	553		
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	V _{GS} = 0 V V _{DS} = 20 V, f = 1 MHz		79	99	рF	
Reverse Transfer Capacitance	C _{rss}]		=.	37	46	•	
Total Gate Charge ^c	Qg			-	8.7	13		
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 20 \text{ V}, I_D = 3.9 \text{ A}$	-	1.4	-	nC	
Gate-Drain Charge ^c	Q _{gd}]		=.	1.6			
Gate Resistance	R _g	f = 1 MHz		1.5	3.0	4.5	Ω	
Turn-On Delay Time ^c	t _{d(on)}	V_{DD} = 20 V, R_L = 20 Ω I_D \cong 1 A, V_{GEN} = 10 V, R_g = 1 Ω		-	7.5	11		
Rise Time ^c	t _r			-	8.4	13	ns	
Turn-Off Delay Time ^c	t _{d(off)}			-	12	18		
Fall Time ^c	t _f			-	5.7	8.5		
Source-Drain Diode Ratings and Chara	acteristics ^b							
Pulsed Current ^a	I _{SM}			-	-	32	Α	
Forward Voltage	V_{SD}	I _F = 5.4 A, V _{GS} = 0 V		-	0.8	1.2	V	

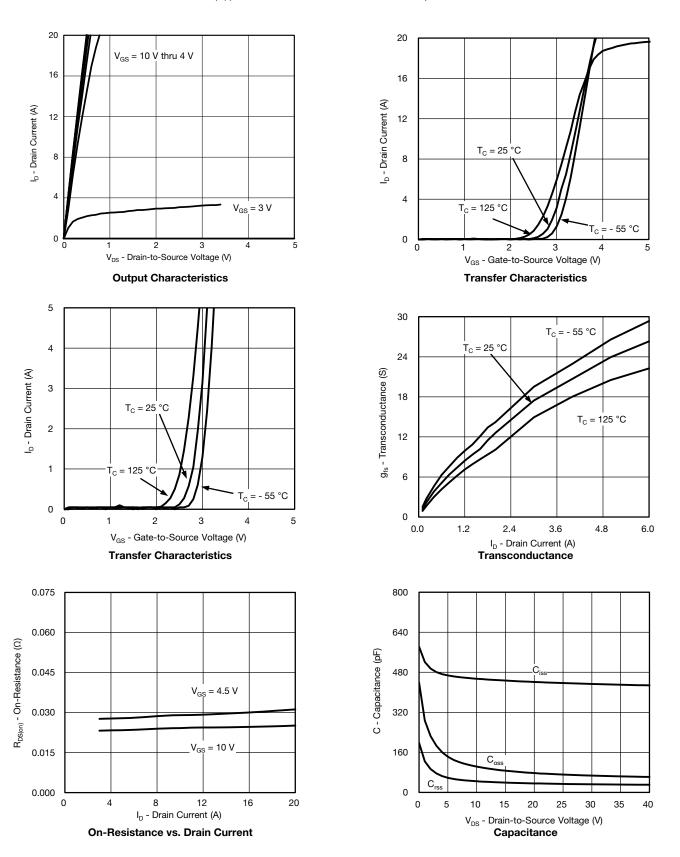
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

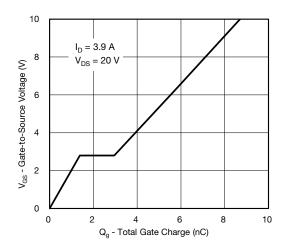


TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

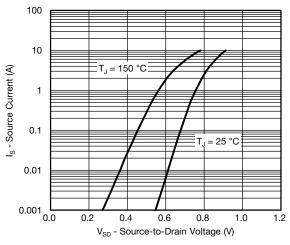




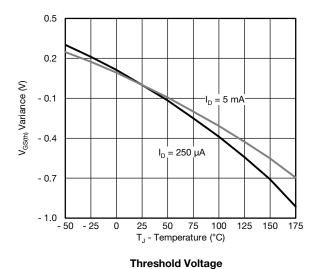
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



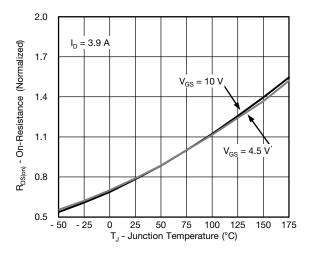
Gate Charge



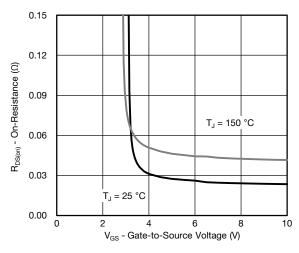
Source Drain Diode Forward Voltage



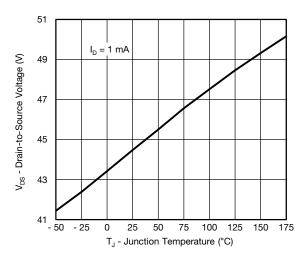
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On-Resistance vs. Junction Temperature



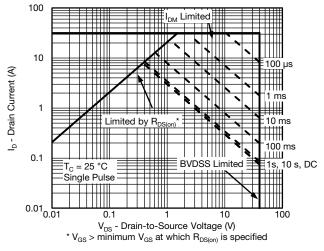
On-Resistance vs. Gate-to-Source Voltage



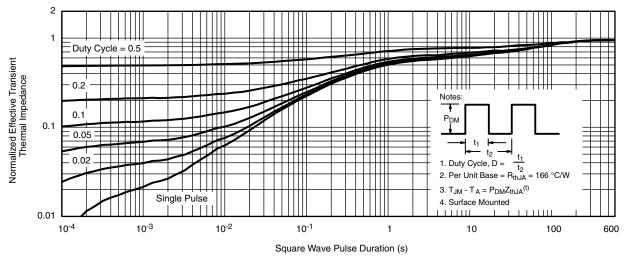
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



Safe Operating Area

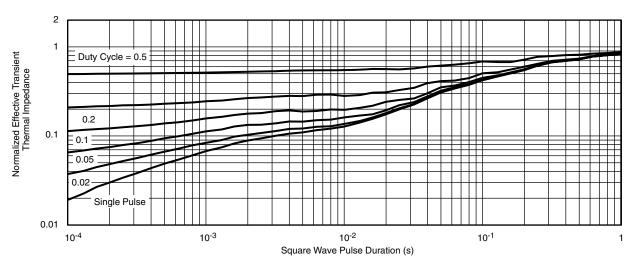


Normalized Thermal Transient Impedance, Junction-to-Ambient

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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



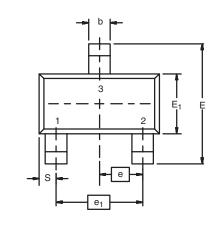
Normalized Thermal Transient Impedance, Junction-to-Foot

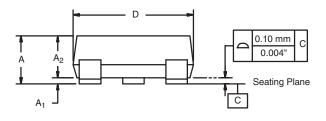
Note

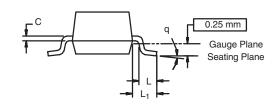
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.



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Dim	MILLIN	IETERS	INCHES		
	Min	Max	Min	Max	
Α	0.89	1.12	0.035	0.044	
A ₁	0.01	0.10	0.0004	0.004	
A ₂	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E ₁	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e ₁	1.90 BSC		0.0748 Ref		
L	0.40	0.60	0.016	0.024	
L ₁	0.64 Ref		0.025 Ref		
S	0.50 Ref		0.020 Ref		
q	3°	8°	3°	8°	
ECN: S-03946-Rev. K. 09-	Jul-01				

DWG: 5479

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RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)



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